

# Omer Gullu

## List of Publications by Year in descending order

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58  
papers

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citations

279798

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docs citations

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times ranked

1038  
citing authors

#	ARTICLE	IF	CITATIONS
1	Morphological and electrical properties of Ag/p-type indium phosphide MIS structures with malachite green organic dyes. , 2022, 18, 421-430.		0
2	Dielectric spectroscopy studies on Al/p-Si photovoltaic diodes with Coomassie Brilliant Blue G-250. Applied Physics A: Materials Science and Processing, 2022, 128, .	2.3	3
3	Barrier enhancement of Al/n-InP Schottky diodes by graphene oxide thin layer. Indian Journal of Physics, 2019, 93, 467-474.	1.8	5
4	Room temperature I-V and C-V characteristics of Au/mTPP/p-Si organic MIS devices. EPJ Applied Physics, 2018, 82, 20101.	0.7	4
5	Synthesis and characterization of vanadium oxide thin films on different substrates. Journal of Materials Science: Materials in Electronics, 2017, 28, 10909-10913.	2.2	11
6	Analysis of interface states of Al/DNA/p-Si MIS photovoltaic structures with DNA biomolecules using the conductance technique. Materials Technology, 2017, 32, 505-513.	3.0	0
7	THE CHARACTERISTIC DIODE PARAMETERS IN Ti/p-InP CONTACTS PREPARED BY DC SPUTTERING AND EVAPORATION PROCESSES OVER A WIDE MEASUREMENT TEMPERATURE. Surface Review and Letters, 2017, 24, 1750052.	1.1	6
8	Wet chemical methods for producing mixing crystalline phase ZrO <sub>2</sub> thin film. Applied Surface Science, 2016, 377, 159-166.	6.1	17
9	The optical characterization of organometallic complex thin films by spectroscopic ellipsometry and photovoltaic diode application. Materials Research Bulletin, 2016, 77, 115-121.	5.2	2
10	Barrier Modification by Methyl Violet Organic Dye Molecules of Ag/P-Inp Structures. European Journal of Interdisciplinary Studies, 2016, 2, 7.	0.1	3
11	Electronic parameters of MIS Schottky diodes with DNA biopolymer interlayer. Materials Science-Poland, 2015, 33, 593-600.	1.0	18
12	Electronic Properties of Cu/n-InP Metal-Semiconductor Structures with Cytosine Biopolymer. Acta Physica Polonica A, 2015, 128, 383-389.	0.5	7
13	Characterization of an Au/n-Si photovoltaic structure with an organic thin film. Materials Science in Semiconductor Processing, 2013, 16, 1125-1130.	4.0	13
14	Current density-voltage analyses and interface characterization in Ag/DNA/p-InP structures. Journal of Applied Physics, 2012, 111, 044503.	2.5	14
15	High barrier Schottky diode with organic interlayer. Solid State Communications, 2012, 152, 381-385.	1.9	64
16	Electronic parameters of high barrier Au/Rhodamine-101/n-Inp Schottky diode with organic interlayer. Thin Solid Films, 2012, 520, 1944-1948.	1.8	38
17	Electronic properties of Al/DNA/p-Si MIS diode: Application as temperature sensor. Journal of Alloys and Compounds, 2011, 509, 571-577.	5.5	37
18	Analysis of electrical and photoelectrical properties of ZnO/p-InP heterojunction. Journal of Alloys and Compounds, 2011, 509, 6631-6634.	5.5	15

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19	Ultrahigh (100%) barrier modification of n-InP Schottky diode by DNA biopolymer nanofilms. <i>Microelectronic Engineering</i> , 2010, 87, 648-651.	2.4	34
20	Electrical analysis of organic dye-based MIS Schottky contacts. <i>Microelectronic Engineering</i> , 2010, 87, 2482-2487.	2.4	57
21	Electrical characterization of the Al/new fuchsin/n-Si organic-modified device. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2010, 42, 1411-1416.	2.7	49
22	Electronic properties of the metal/organic interlayer/inorganic semiconductor sandwich device. <i>Journal of Physics and Chemistry of Solids</i> , 2010, 71, 351-356.	4.0	47
23	A study of the rectifying behaviour of aniline green-based Schottky diode. <i>Microelectronic Engineering</i> , 2010, 87, 187-191.	2.4	9
24	Silicon MIS diodes with Cr <sub>2</sub> O <sub>3</sub> nanofilm: Optical, morphological/structural and electronic transport properties. <i>Applied Surface Science</i> , 2010, 256, 4185-4191.	6.1	28
25	Electrical properties of safranin T/p-Si organic/inorganic semiconductor devices. <i>EPJ Applied Physics</i> , 2010, 50, 10401.	0.7	6
26	n-type InP Schottky diodes with organic thin layer: Electrical and interfacial properties. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2010, 28, 466-472.	1.2	7
27	Current-voltage and capacitance-voltage characteristics of Fe/p-InP Schottky barriers. <i>International Journal of Electronics</i> , 2010, 97, 973-983.	1.4	4
28	Optical and structural properties of CuO nanofilm: Its diode application. <i>Journal of Alloys and Compounds</i> , 2010, 492, 378-383.	5.5	156
29	Electrical analysis of organic interlayer based metal/interlayer/semiconductor diode structures. <i>Journal of Applied Physics</i> , 2009, 106, .	2.5	54
30	Impedance and Interface Properties of Al/Methyl-Red/p-InP Solar Cell. <i>International Journal of Photoenergy</i> , 2009, 2009, 1-7.	2.5	7
31	Fabrication and electrical characterization of a silicon Schottky device based on organic material. <i>Physica Scripta</i> , 2009, 79, 035802.	2.5	21
32	Electrical Properties of Organic-Inorganic Semiconductor Device Based on Rhodamine-101. <i>Journal of Electronic Materials</i> , 2009, 38, 1995-1999.	2.2	7
33	Determination of the laterally homogeneous barrier height of metal/p-InP Schottky barrier diodes. <i>Vacuum</i> , 2009, 83, 1470-1474.	3.5	25
34	Analysis of the series resistance and interface state densities in metal semiconductor structures. <i>Journal of Physics: Conference Series</i> , 2009, 153, 012054.	0.4	15
35	Electrical Characteristics of Co/n-Si Schottky Barrier Diodes Using $I-V$ and $C-V$ Measurements. <i>Chinese Physics Letters</i> , 2009, 26, 067301.	3.3	10
36	The analysis of lateral distribution of barrier height in identically prepared Co/n-Si Schottky diodes. <i>Journal of Alloys and Compounds</i> , 2009, 486, 343-347.	5.5	20

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37	Laterally inhomogeneous barrier analysis of the methyl violet/p-Si organic/inorganic hybrid Schottky structures. <i>Applied Surface Science</i> , 2008, 254, 3039-3044.	6.1	61
38	Determination of the laterally homogeneous barrier height of thermally annealed and unannealed Au/p-InP/Zn-Au Schottky barrier diodes. <i>Applied Surface Science</i> , 2008, 254, 3558-3561.	6.1	27
39	Photovoltaic and electronic properties of quercetin/p-InP solar cells. <i>Solar Energy Materials and Solar Cells</i> , 2008, 92, 1205-1210.	6.2	72
40	Electrical characteristics and inhomogeneous barrier analysis of aniline green/p-Si heterojunctions. <i>Journal of Materials Science: Materials in Electronics</i> , 2008, 19, 986-991.	2.2	17
41	Fabrication and electrical characteristics of Schottky diode based on organic material. <i>Microelectronic Engineering</i> , 2008, 85, 1647-1651.	2.4	144
42	DNA-based organic-on-inorganic devices: Barrier enhancement and temperature issues. <i>Microelectronic Engineering</i> , 2008, 85, 2250-2255.	2.4	18
43	Fabrication and electrical properties of Al/aniline green/n-Si/AuSb structure. <i>Materials Science in Semiconductor Processing</i> , 2008, 11, 53-58.	4.0	19
44	Temperature dependence of current-voltage characteristics of Sn/p-Si Schottky contacts. <i>Physica B: Condensed Matter</i> , 2008, 403, 131-138.	2.7	13
45	$\gamma$ -Irradiation-induced changes at the electrical characteristics of Sn/p-Si Schottky contacts. <i>Vacuum</i> , 2008, 82, 789-793.	3.5	22
46	Fabrication and electrical properties of Al/phenolsulfonphthalein/n-Si/AuSb structure. <i>Vacuum</i> , 2008, 82, 1264-1268.	3.5	11
47	Effects of the barrier metal thickness and hydrogen pre-annealing on the characteristic parameters of Au/n-GaAs metal-semiconductor Schottky contacts. <i>Thin Solid Films</i> , 2008, 516, 7851-7856.	1.8	8
48	DNA-based organic-on-inorganic semiconductor Schottky structures. <i>Applied Surface Science</i> , 2008, 254, 5175-5180.	6.1	34
49	Determination of lateral barrier height of identically prepared Ni/n-type Si Schottky barrier diodes by electrodeposition. <i>Physica B: Condensed Matter</i> , 2008, 403, 2211-2214.	2.7	23
50	Electron irradiation effects on the organic-on-inorganic silicon Schottky structure. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , 2008, 593, 544-549.	1.6	16
51	Temperature-dependent behavior of Ti/p-InP/ZnAu Schottky barrier diodes. <i>Semiconductor Science and Technology</i> , 2008, 23, 035006.	2.0	17
52	Gamma irradiation-induced changes at the electrical characteristics of organic-based schottky structures. <i>Journal Physics D: Applied Physics</i> , 2008, 41, 135103.	2.8	31
53	Fabrication and electrical properties of organic-on-inorganic Schottky devices. <i>Journal of Physics Condensed Matter</i> , 2008, 20, 215210.	1.8	21
54	Fabrication and electrical properties of Al/Safranin T/n-Si/AuSb structure. <i>Semiconductor Science and Technology</i> , 2008, 23, 075005.	2.0	37

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55	Electrical characterization of organic-on-inorganic semiconductor Schottky structures. Journal of Physics Condensed Matter, 2008, 20, 045215.	1.8	25
56	DNA-modified indium phosphide Schottky device. Applied Physics Letters, 2008, 92, 212106.	3.3	30
57	Electrical characteristics of the hydrogen pre-annealed Au/n-GaAs Schottky barrier diodes as a function of temperature. Applied Surface Science, 2007, 253, 7246-7253.	6.1	24
58	The effect of Schottky metal thickness on barrier height inhomogeneity in identically prepared Au/n-GaAs Schottky diodes. Semiconductor Science and Technology, 2006, 21, 1-5.	2.0	71